## 1. General description

NPN high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- Electrically similar to popular MJD148 series
- · Low collector emitter saturation voltage
- Fast switching speeds
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Power management
- · Load switch
- Linear mode voltage regulator
- Constant current drive backlighting application
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	45	V
I <sub>C</sub>	collector current		-	-	4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	7	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 1 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	85	-	375	
		$V_{CE}$ = 1 V; $I_{C}$ = 3 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	30	-	-	



### 45 V, 4 A NPN high power bipolar transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector		Ę
3	Е	emitter		в - [
mb	С	mounting base; connected to collector	1 3	C; mb aaa-029889
			DPAK (SOT428C)	

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
MJD148-Q		Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
MJD148-Q	MJD148A

# 8. Limiting values

#### Table 5. Limiting values

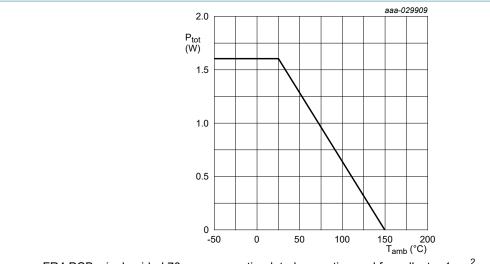
In accordance with the Absolute Maximum Rating System (IEC601134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	7	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C	[1]	-	15	W
		T <sub>amb</sub> ≤ 25 °C	[2]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Total power dissipation junction to mounting base.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 μm copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

### 45 V, 4 A NPN high power bipolar transistor



FR4 PCB, single-sided 70 µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Fig. 1. Power derating curves SOT428C

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	79	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	9	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 µm copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

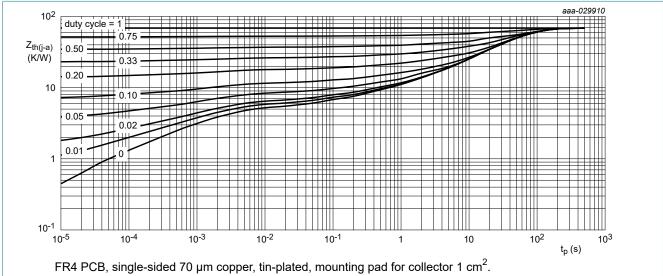


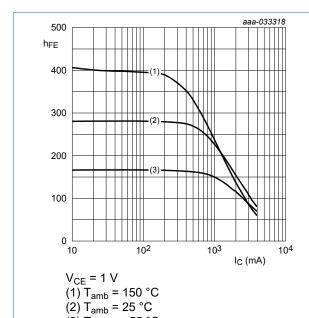
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 45 V, 4 A NPN high power bipolar transistor

## 10. Characteristics

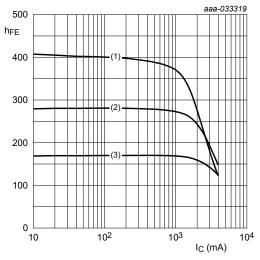
**Table 7. Characteristics** 

Symbol	Parameter	Conditions	N	Vlin	Тур	Max	Unit
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 45 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	•	-	1	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-		-	1	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	4	10	-	-	
		$V_{CE}$ = 1 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	8	35	-	375	
		$V_{CE}$ = 1 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	5	50	-	-	
		$V_{CE}$ = 1 V; $I_{C}$ = 3 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	3	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 2 A; $I_B$ = 0.2 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-		-	0.5	V
$V_{BE}$	base-emitter voltage	$V_{CE}$ = 1 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $T_{amb}$ = 25 °C	-		-	1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = 1 V; $I_{C}$ = 250 mA; f = 100 MHz; $T_{amb}$ = 25 °C	3	3	-	-	MHz



DC current gain as a function of collector Fig. 3. current; typical values

(3)  $T_{amb} = -55 \, ^{\circ}C$ 



V<sub>CE</sub> = 10 V (1) T<sub>amb</sub> = 150 °C (2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 4. DC current gain as a function of collector current; typical values

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#### 45 V, 4 A NPN high power bipolar transistor

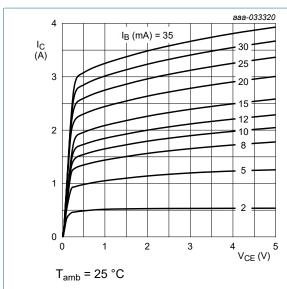
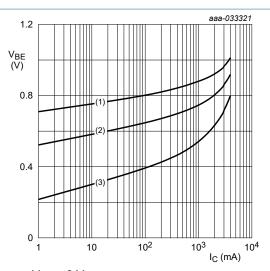
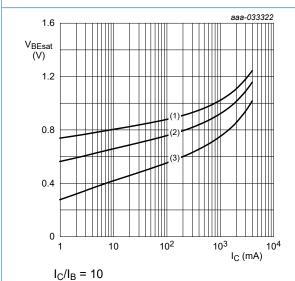


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



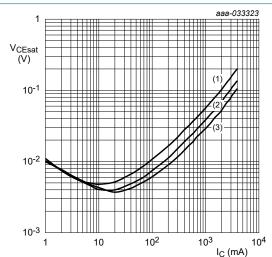
V<sub>CE</sub> = 2 V (1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 150 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



(1)  $T_{amb} = -55 \text{ °C}$ (2)  $T_{amb} = 25 \text{ °C}$ (3)  $T_{amb} = 150 \text{ °C}$ 

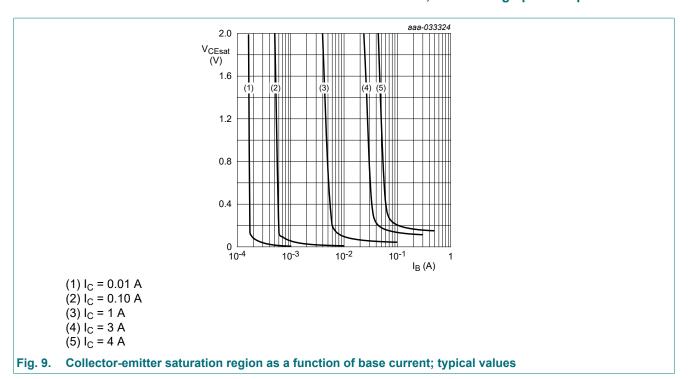
Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ (1)  $T_{\rm amb} = 150~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ 

ig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

### 45 V, 4 A NPN high power bipolar transistor

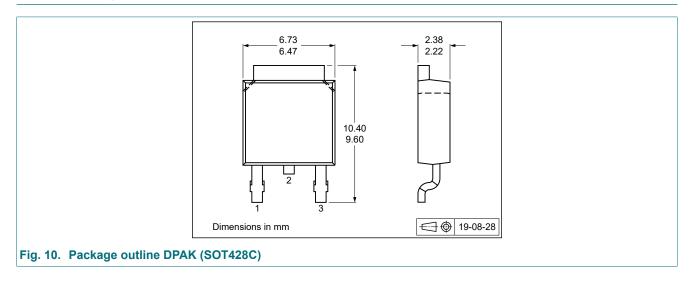


## 11. Test information

## **Quality information**

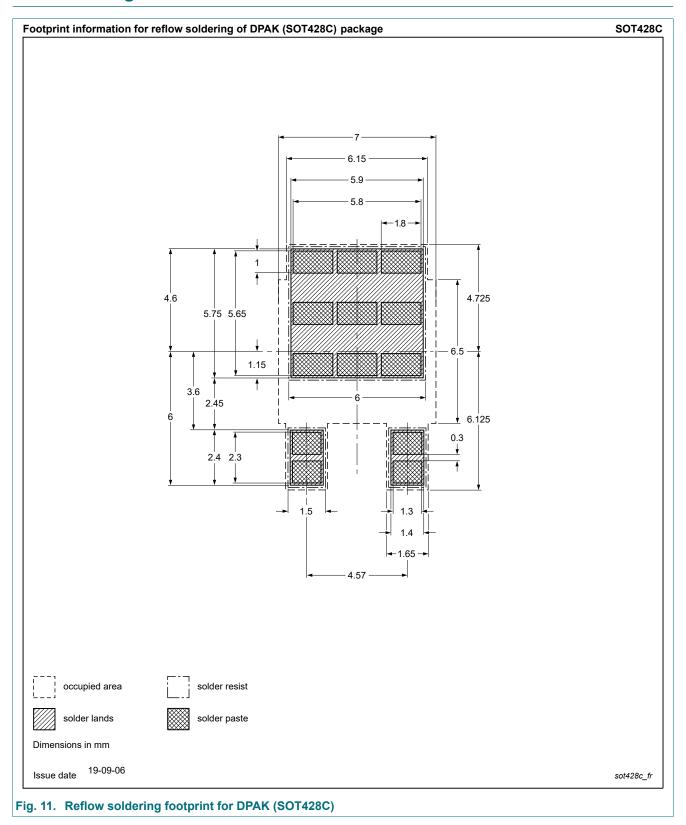
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



45 V, 4 A NPN high power bipolar transistor

# 13. Soldering



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## 45 V, 4 A NPN high power bipolar transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
MJD148-Q v.1	20210517	Product data sheet	-	-

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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MJD148-Q

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